

IN THE ABSTRACT:

Please delete the existing abstract and replace the following abstract as follows:

ABSTRACT

A first intermediate body is fabricated on a semiconductor substrate. The first intermediate body includes a first lasing portion of a multi-layer stack and a metal adherent layer. A second intermediate body is fabricated on a support substrate. The second intermediate body includes a second lasing portion formed of a multi-layer stack to be less in size than the first lasing portion, and a groove formed adjacent thereto to form a metal adherent layer. Then, with waveguide paths brought into close proximity, the adherent layers of the first and second intermediate bodies are fused to generate an integrated adherent layer, thereby securely adhering the first and second lasing portions to each other. Thereafter, the support substrate is stripped off from the second lasing portion, thereby allowing the adherent layer to be partially exposed. A semiconductor laser device is thus fabricated which has the exposed adherent layer as a common electrode.